

General Description:

The LW4227A5 uses trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is TO-263, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- Power switch circuit Power
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

100% DVDS Tested

100% Avalanche Tested



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
4227/LW A5/D.C.	LW4227A5	TO-263	Reel	800 Pcs

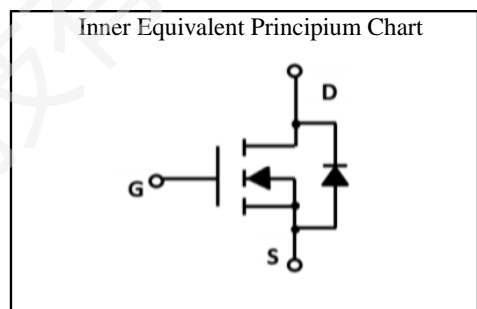
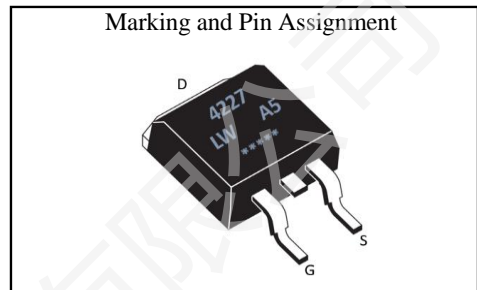
Absolute Maximum Ratings:

Symbol	Parameter	Value	Units
V_{DSS}	Drain-to-Source Voltage	200	V
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	67
	Continuous Drain Current	$T_C=100^\circ\text{C}$	42
I_{DM}^{a1}	Pulsed Drain Current	268	A
E_{AS}^{a2}	Single Pulse Avalanche Energy	210	mJ
I_{AS}^{a2}	Avalanche Current	48	A
V_{GS}	Gate-to-Source Voltage	± 30	V
P_D	Power Dissipation	278	W
T_J, T_{STG}	Operating Junction and Storage Temperature Rang	150, -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	260	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.45	$^\circ\text{C}/\text{W}$
$R_{\theta JA}^{a3}$	Thermal Resistance, Junction-to-Ambient	62	$^\circ\text{C}/\text{W}$

V_{DSS}	200	V
I_D	67	A
P_D	278	W
$R_{DS(ON) \text{ TYPE}}$	18	$\text{m}\Omega$



Electrical Characteristic ($T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	200	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=200V, V_{GS}=0V$	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	3.6	4.2	5.0	V
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=40A$	--	18	22	$m\Omega$

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V$	--	7468	--	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	--	512	--	
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	--	224	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	1.5	--	Ω

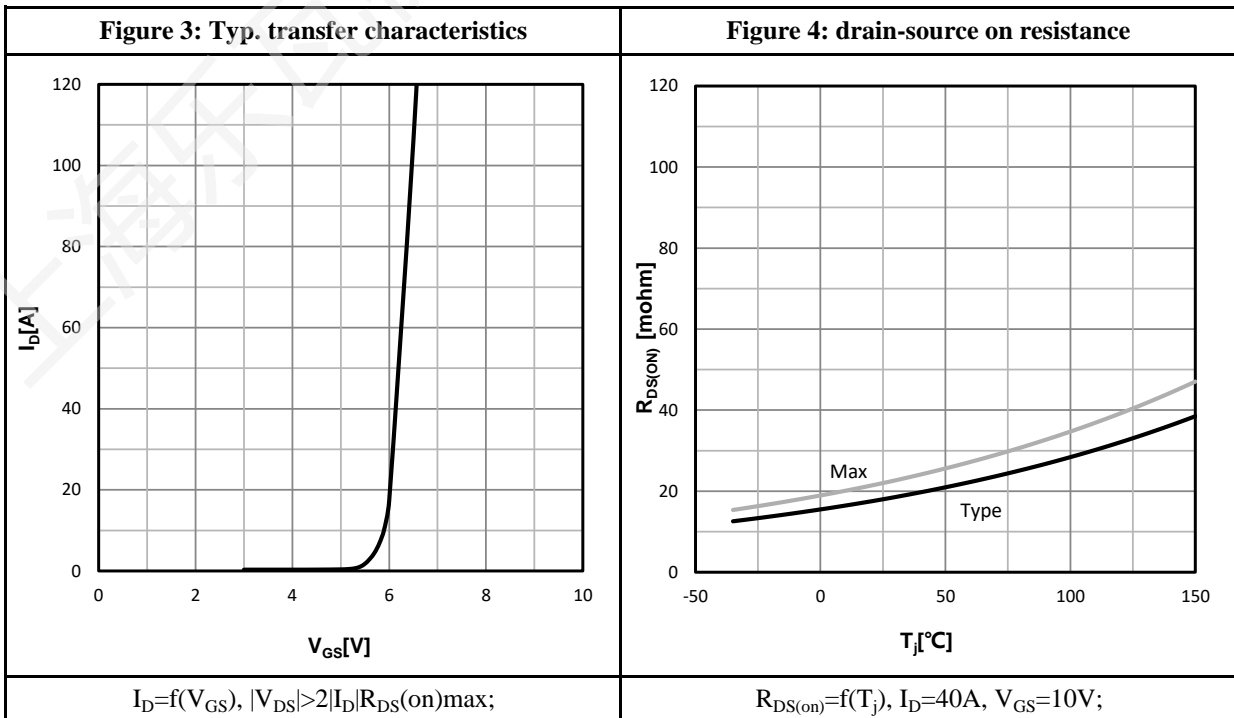
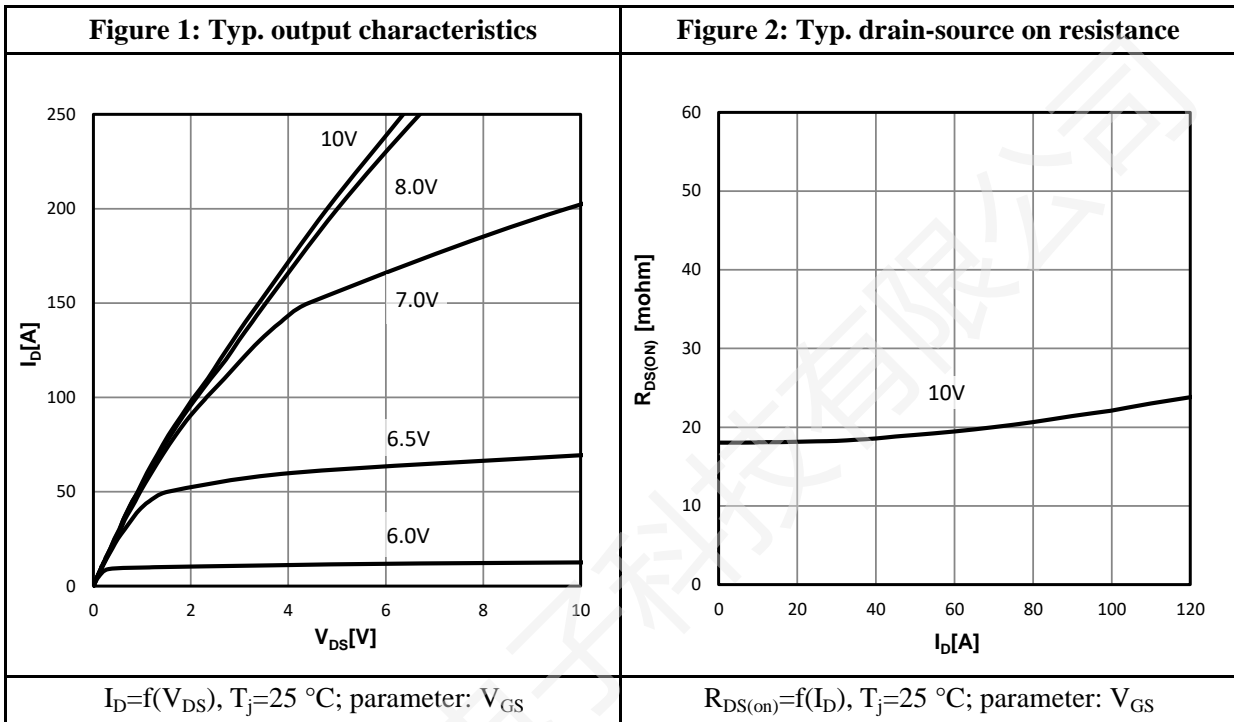
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=46A$	--	42	--	ns
t_r	Rise Time	$V_{DS}=100V$	--	31	--	
$t_{d(OFF)}$	Turn-Off Delay Time	$V_{GS}=10V$	--	50	--	
t_f	Fall Time	$R_G=2.5\Omega$	--	32	--	
Q_g	Total Gate Charge	$V_{GS}=10V$	--	128	--	nC
Q_{gs}	Gate to Source Charge	$V_{DS}=100V$	--	44	--	
Q_{gd}	Gate to Drain Charge	$I_D=46A$	--	44	--	

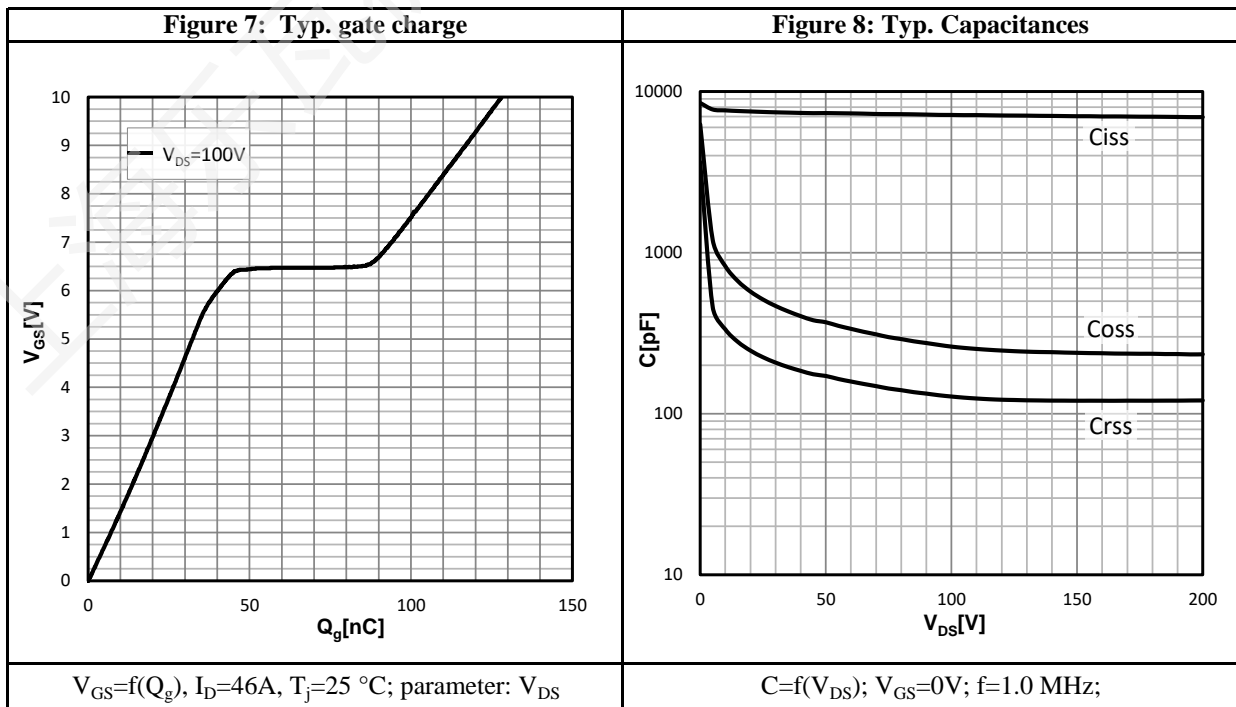
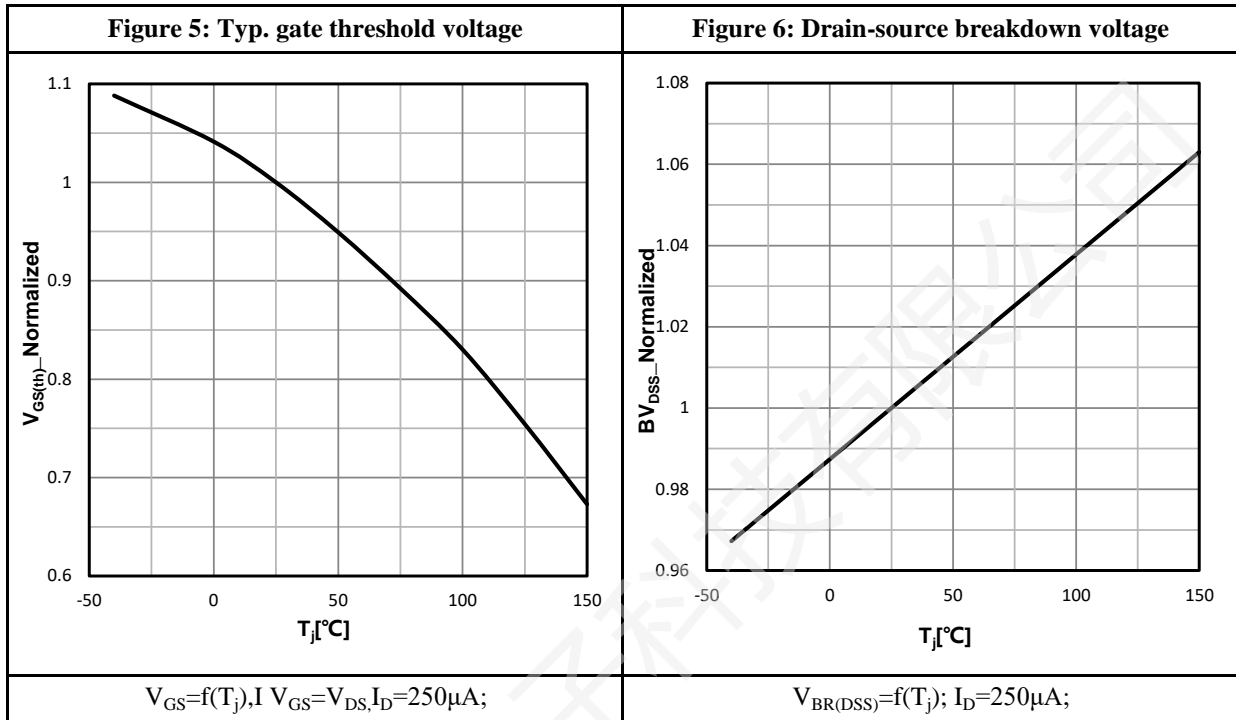
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C=25\text{ }^\circ\text{C}$	--	--	67	A
V_{SD}	Diode Forward Voltage	$I_S=40A, V_{GS}=0V$	--	--	1.2	V
t_{rr}	Reverse Recovery Time	$I_S=30A, V_{DD}=50V$	--	110	--	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	--	550	--	nC

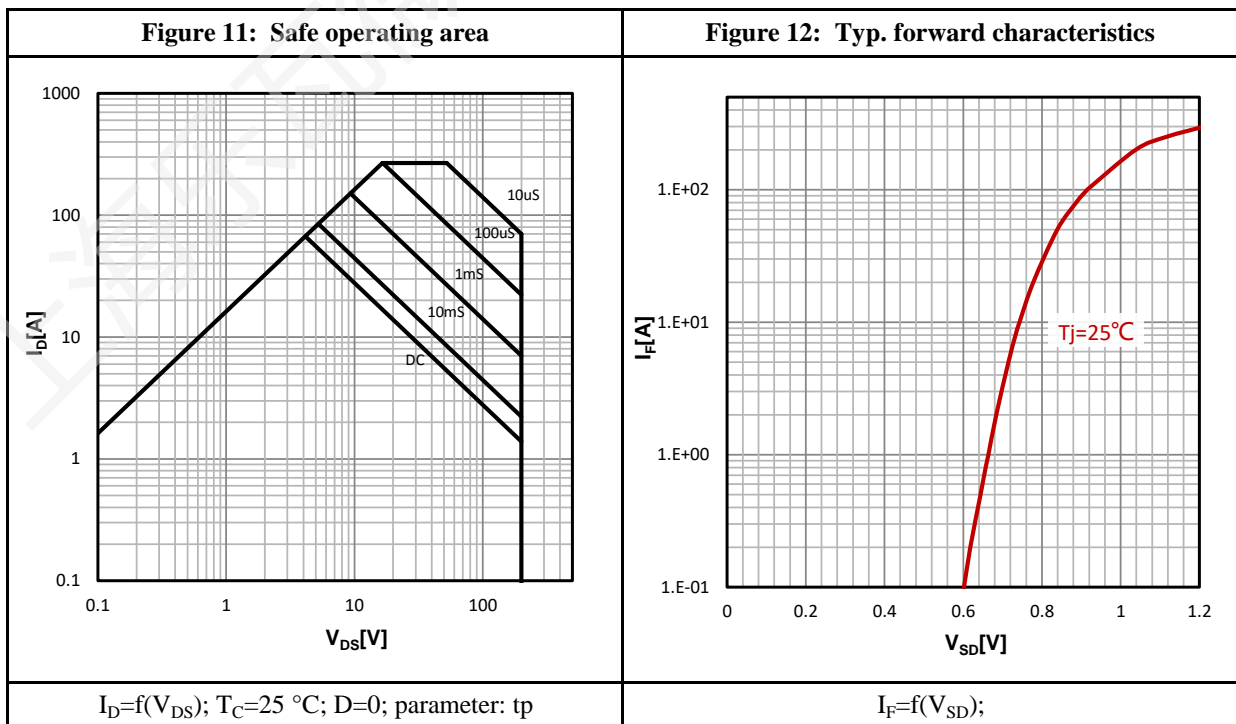
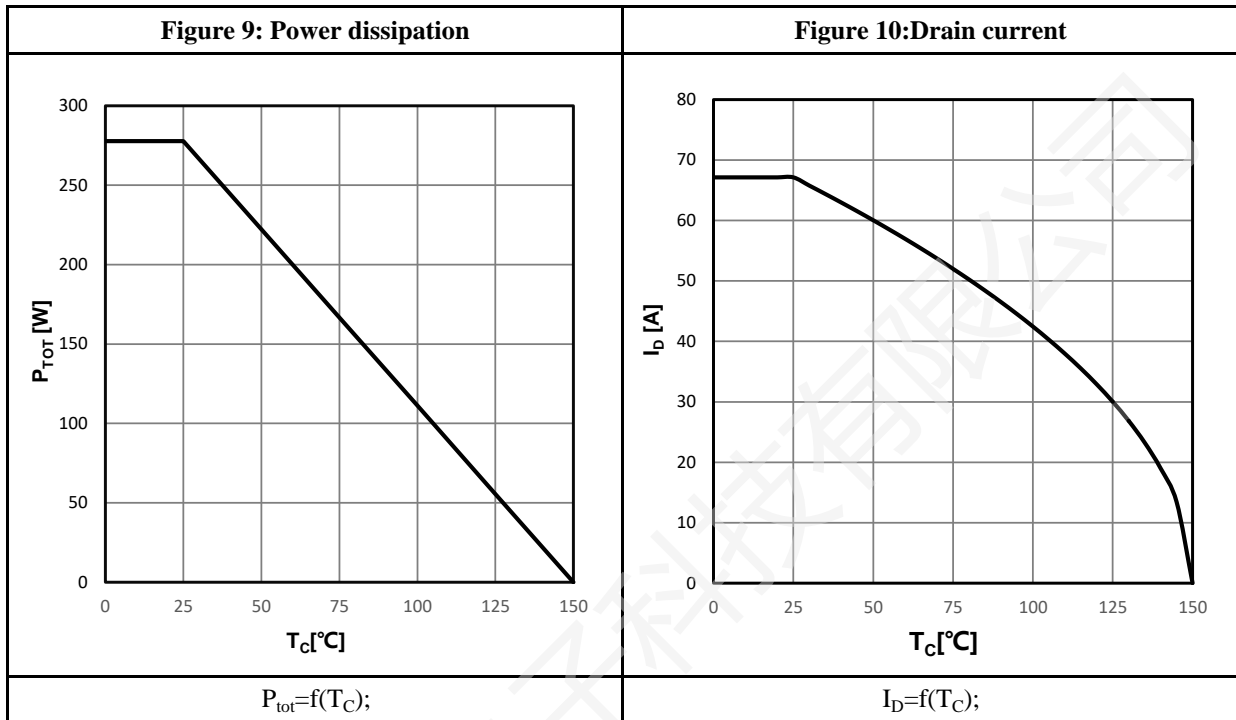
a1: Repetitive rating; pulse width limited by maximum junction temperature

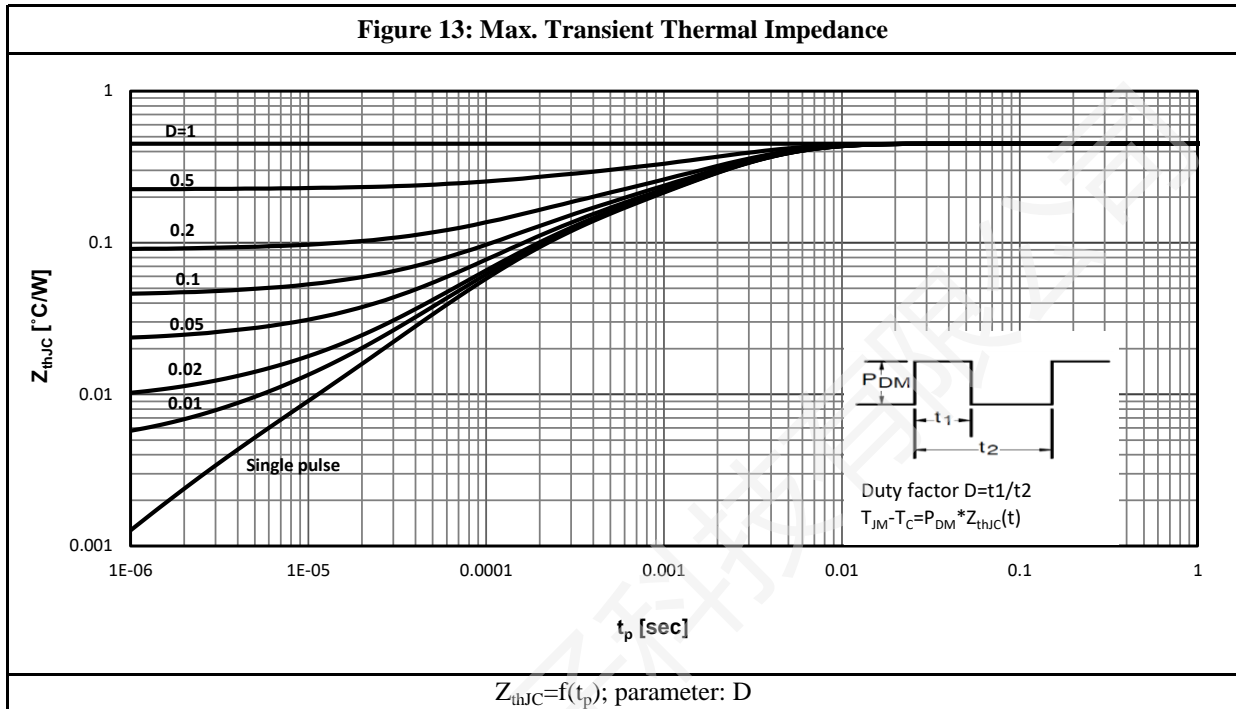
a2: $V_{DD}=100V, L=0.18mH, R_G=25\Omega$, Starting $T_j=25\text{ }^\circ\text{C}$

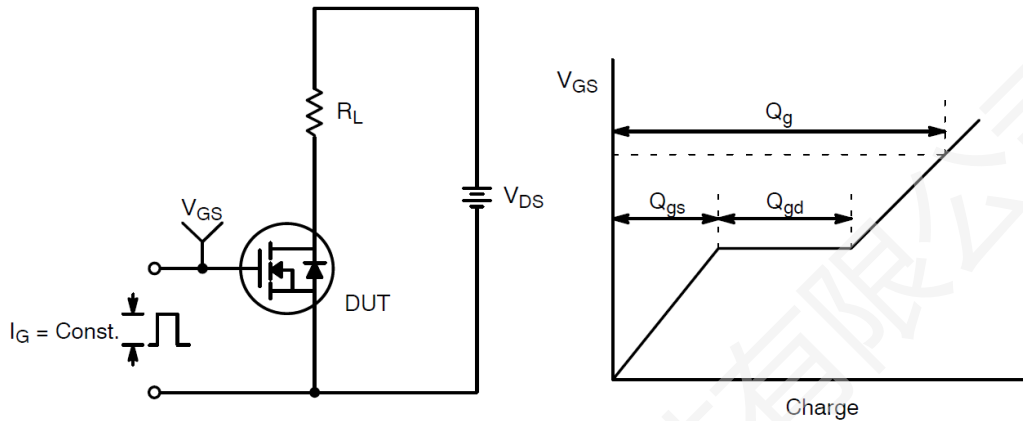
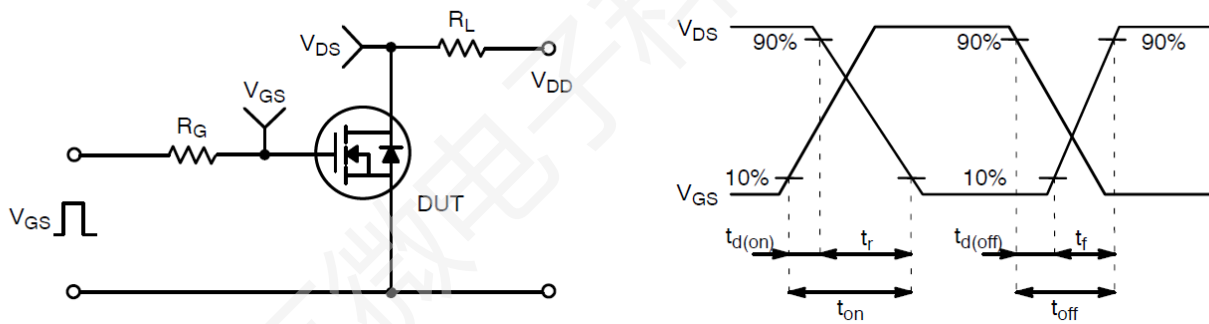
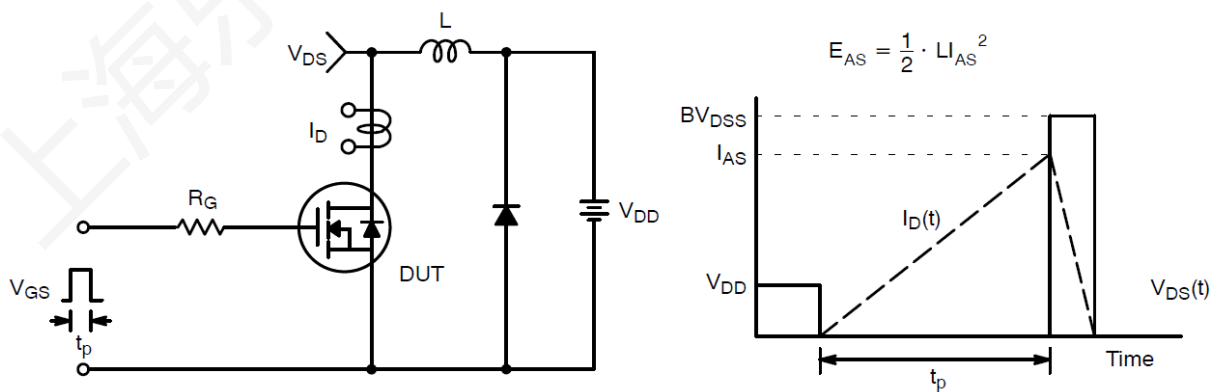
a3: Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection.

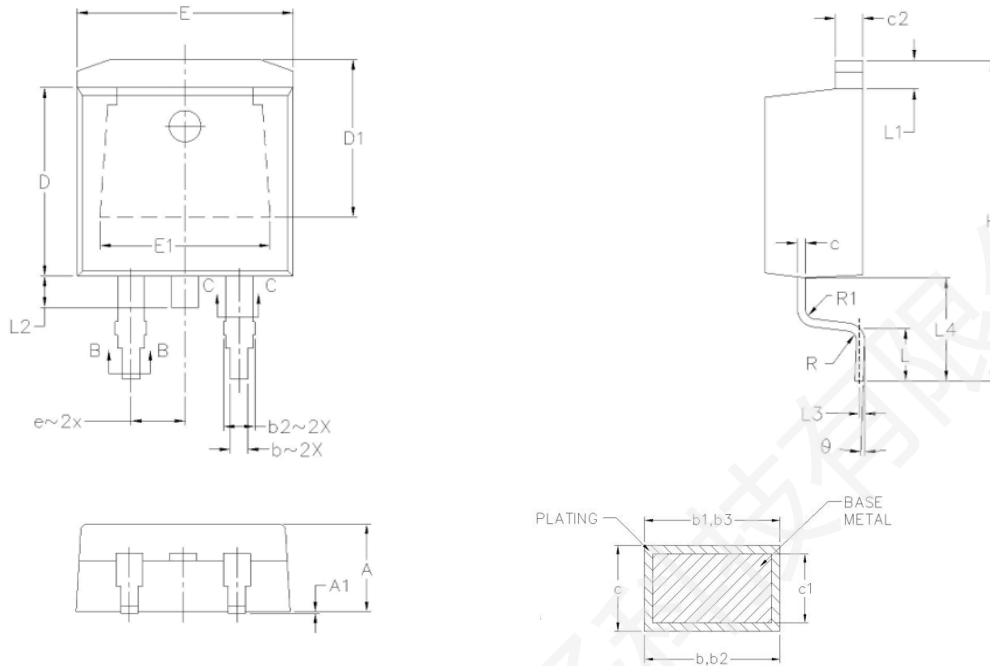
Characteristics Curve:








Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:


Symbol	COMMON			
	MM		INCH	
	Min	Max	Min	Max
A	4.064	4.826	0.160	0.190
A1	0.000	0.254	0.000	0.010
b	0.508	0.991	0.020	0.039
b1	0.508	0.889	0.020	0.035
b2	1.143	1.778	0.045	0.070
b3	1.143	1.727	0.045	0.068
c	0.381	0.737	0.015	0.029
c1	0.381	0.584	0.015	0.023
c2	1.143	1.651	0.045	0.065
D	8.382	9.652	0.330	0.380
D1	6.858	—	0.270	—
E	9.652	10.668	0.380	0.420
E1	6.223	—	0.245	—
e	2.540 BSC		0.100 BSC	
H	14.605	15.875	0.575	0.625
L	1.778	2.794	0.070	0.110
L1	—	1.676	—	0.066
L2	—	1.778	—	0.070
L3	0.254 BSC		0.010 BSC	
L4	4.780	5.280	0.188	0.208
R	0.460 TYP		0.018 TYP	
R1	0.461 TYP		0.019 TYP	
theta	0°	8°	0°	8°

Revision History:

Revison	Date	Descriptions
Rev 1.0	July.2025	Initial Version

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